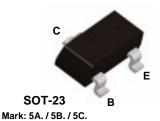


### Discrete POWER & Signal **Technologies**

BC807-16 BC807-25 BC807-40



## **PNP General Purpose Amplifier**

This device is designed for general purpose amplifier and switching applications at currents to 1.0 A. Sourced from Process 78.

### **Absolute Maximum Ratings\***

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	45	V
V <sub>CES</sub>	Collector-Base Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	1.2	А
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.

  2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BC807-16 / -25 / -40	
$P_D$	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/∘C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

### **PNP General Purpose Amplifier**

(continued)

Electrical Characteristics TA = 25°C unless otherwise noted						
Symbol	Parameter	Test Conditions	Min	Max	Units	
OFF CHARACTERISTICS						
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	45		V	
V <sub>(BR)CES</sub>	Collector-Base Breakdown Voltage	$I_C = 100  \mu A,  I_E = 0$	50		V	
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A},  I_C = 0$	5.0		V	
I <sub>CBO</sub>	Collector-Cutoff Current	V <sub>CB</sub> = 20 V V <sub>CB</sub> = 20 V, T <sub>A</sub> = 150°C		100 5.0	nA μA	
ON CHARACTERISTICS						
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 1.0 V - 16 - 25 - 40	100 160 250	250 400 600		

 $I_C = 500 \text{ mA}, V_{CE} = 1.0 \text{ V}$ 

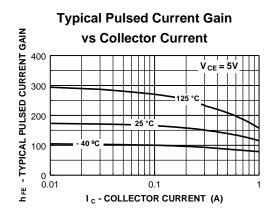
 $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ 

 $I_C = 500 \text{ mA}, V_{CE} = 1.0 \text{ V}$ 

### **Typical Characteristics**

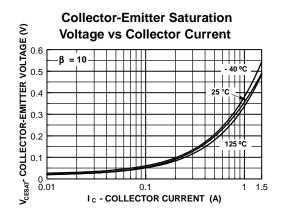
 $V_{\text{CE(sat)}} \\$ 

V<sub>BE(on)</sub>



Collector-Emitter Saturation Voltage

Base-Emitter On Voltage



40

0.7

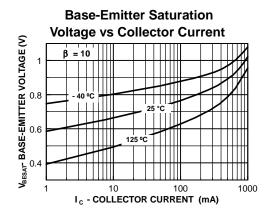
1.2

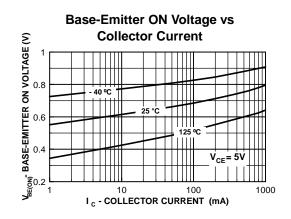
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### **PNP General Purpose Amplifier**

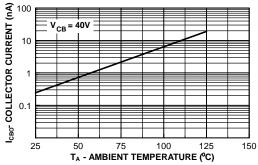
(continued)

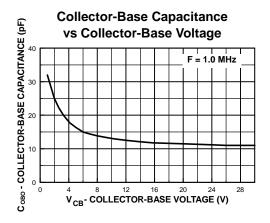
### Typical Characteristics (continued)



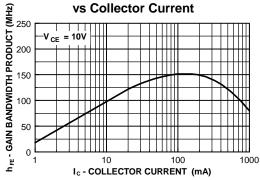




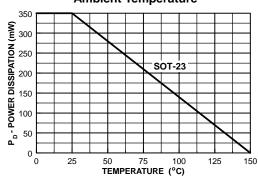




# Gain Bandwidth Product vs Collector Current



### Power Dissipation vs Ambient Temperature



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E<sup>2</sup>CMOS<sup>™</sup> PowerTrench<sup>™</sup>

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 $\begin{array}{lll} \mathsf{FACT} \ \mathsf{Quiet} \ \mathsf{Series^{\mathsf{TM}}} & \mathsf{Quiet} \ \mathsf{Series^{\mathsf{TM}}} \\ \mathsf{FAST}^{\otimes} & \mathsf{SuperSOT^{\mathsf{TM}}}\text{-}3 \\ \mathsf{FASTr^{\mathsf{TM}}} & \mathsf{SuperSOT^{\mathsf{TM}}}\text{-}6 \\ \mathsf{GTO^{\mathsf{TM}}} & \mathsf{SuperSOT^{\mathsf{TM}}}\text{-}8 \\ \mathsf{HiSeC^{\mathsf{TM}}} & \mathsf{TinyLogic^{\mathsf{TM}}} \end{array}$ 

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